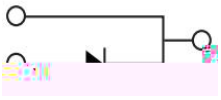
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TriQSiC™ 1200V Silicon Carbide Schottky Diode

Features

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Benefits

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Applications

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Table 1 Key performance and package parameters

Type	V_{RRM}	I_F	Q_C	Marking	Package

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1200V SiC Schottky Diode

1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note

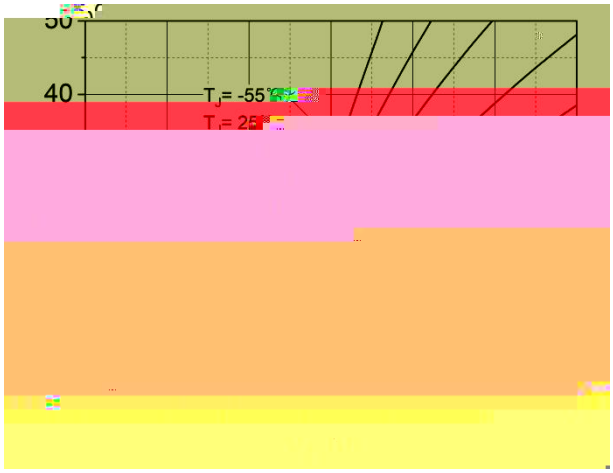
2 Thermal characterir

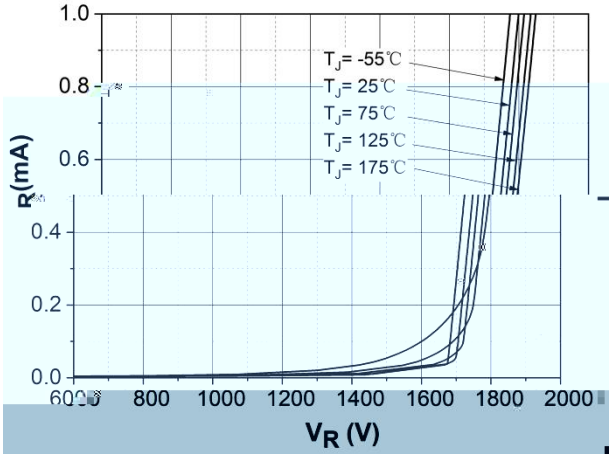
3 Electrical characteristics

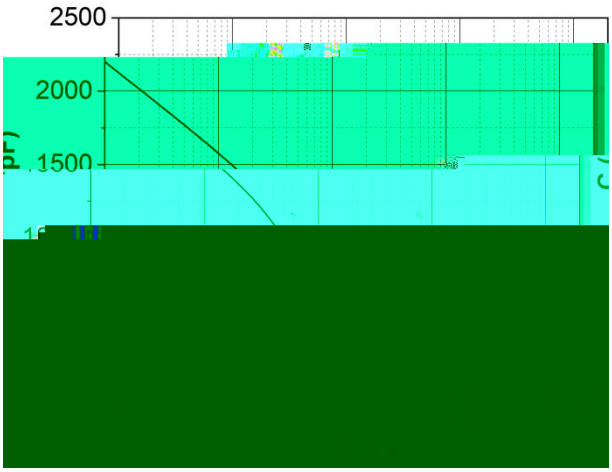
Table 4 Electrical characteristics

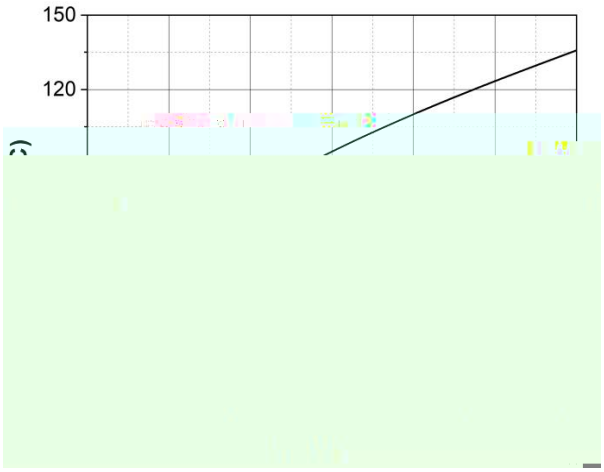
Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note

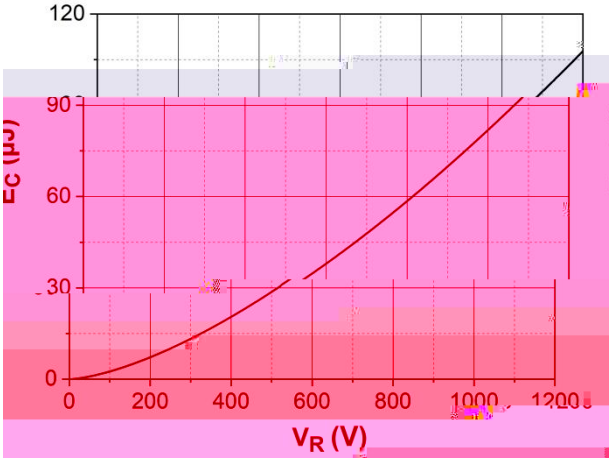
4 Electrical characteristic diagrams

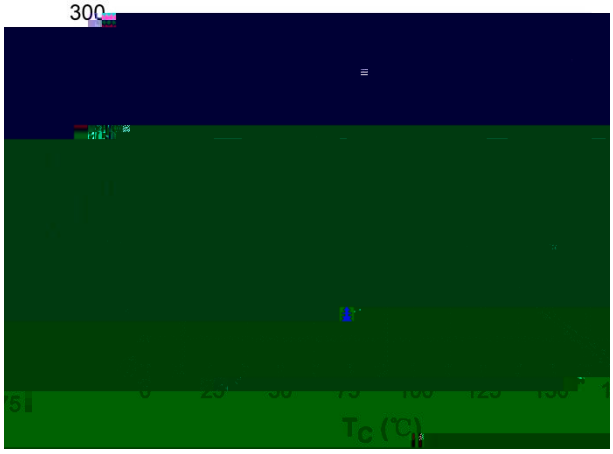




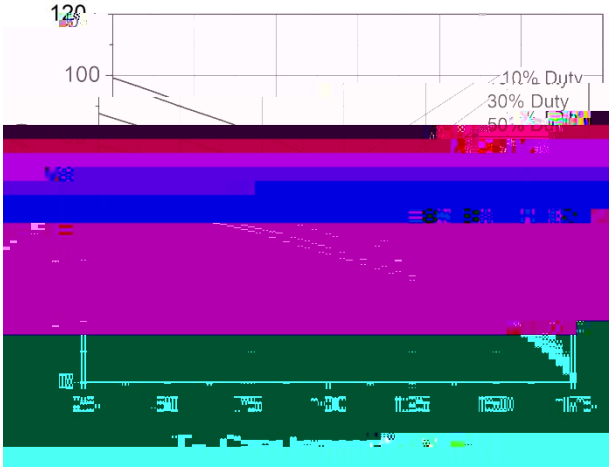


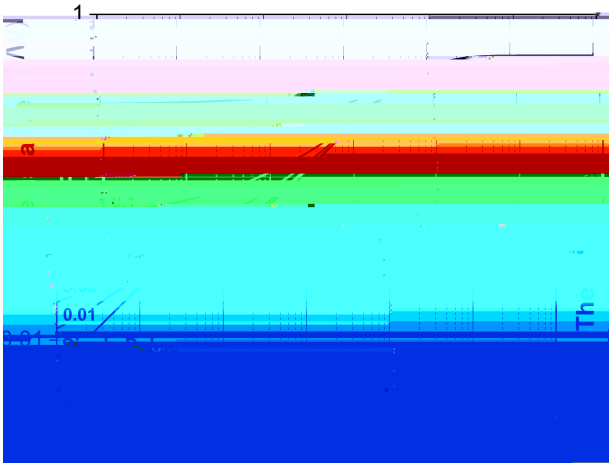






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1200V SiC Schottky

Revision history

Document version	Date of release	Document stage	Description of changes
V02_00	2024-08-05	——	——
V02_01	2024-08-07	——	——
V02_02	2024-10-28	——	——
V02_03	2025-04-30	——	——
V02_04	2025-05-23	——	——
V03_00	2026-05-12	Final	——

Attention

RoHS compliance

REACH compliance

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